

PSMN6R5-80PS

N-channel 80V 6.9mΩ standard level MOSFET in TO220

Rev. 01 — 9 March 2010

Objective data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Motor control
- Load switching
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	-	80	V
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1	[1]	-	100	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	-	210	W
T_j	junction temperature		-55	-	175	°C
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 49\text{ A}$; $V_{sup} \leq 80\text{ V}$; $R_{GS} = 50\text{ }\Omega$; unclamped	-	-	700	mJ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$;	-	16	-	nC
$Q_{G(\text{tot})}$	total gate charge	$V_{DS} = 40\text{ V}$; see Figure 14 and 15	-	71	-	nC
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; see Figure 13	[2]	-	5.9	6.9 mΩ

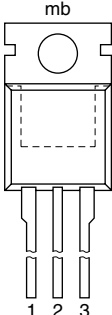
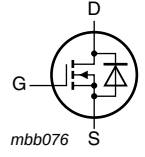
[1] Continuous current rating is limited by package.

[2] Measured 3 mm from package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

SOT78 (TO-220AB)

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
PSMN6R5-80PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

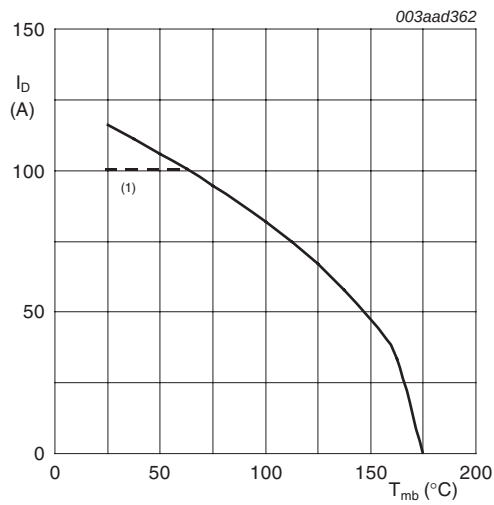
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	80	V
V_{DGR}	drain-gate voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	80	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ °C}$; see Figure 1	-	82	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; see Figure 1 ^[1]	-	100	A
I_{DM}	peak drain current	$t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$; see Figure 3	-	470	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	210	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
Source-drain diode					
I_S	source current	$T_{mb} = 25\text{ °C}$	-	100	A
I_{SM}	peak source current	$t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$	-	470	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 49\text{ A}$; $V_{sup} \leq 80\text{ V}$; $R_{GS} = 50\text{ }\Omega$; unclamped	-	700	mJ

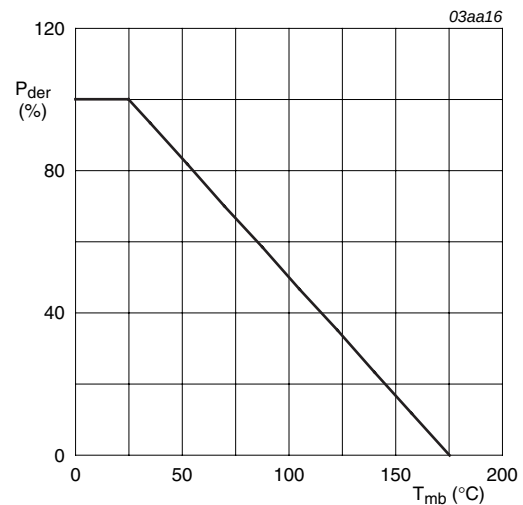
[1] Continuous current rating is limited by package.



$$V_{GS} \geq 10V$$

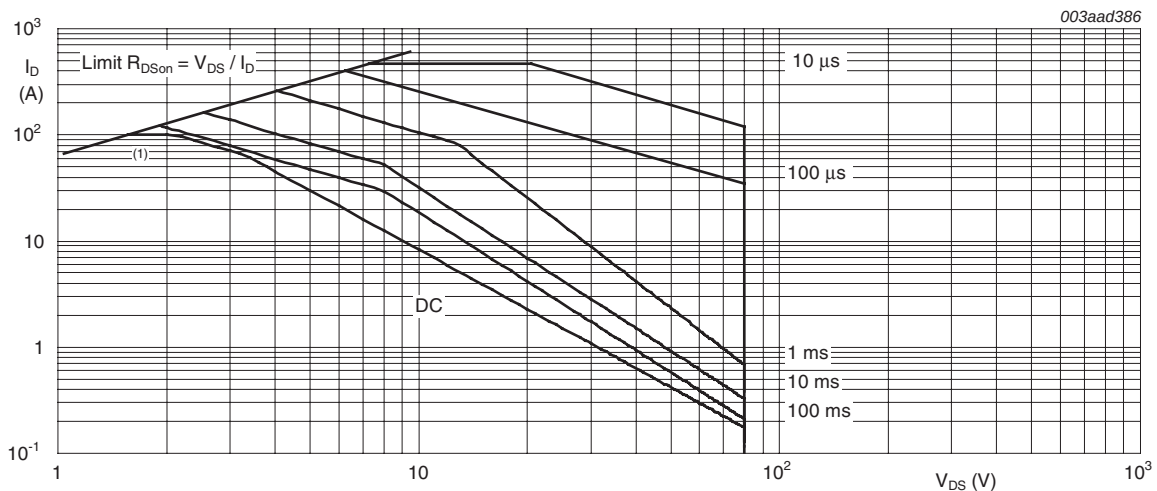
(1) Capped at 100 A due to package.

Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$$V_{GS} \geq 10V$$

(1) Capped at 100 A due to package.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.4	0.7	K/W

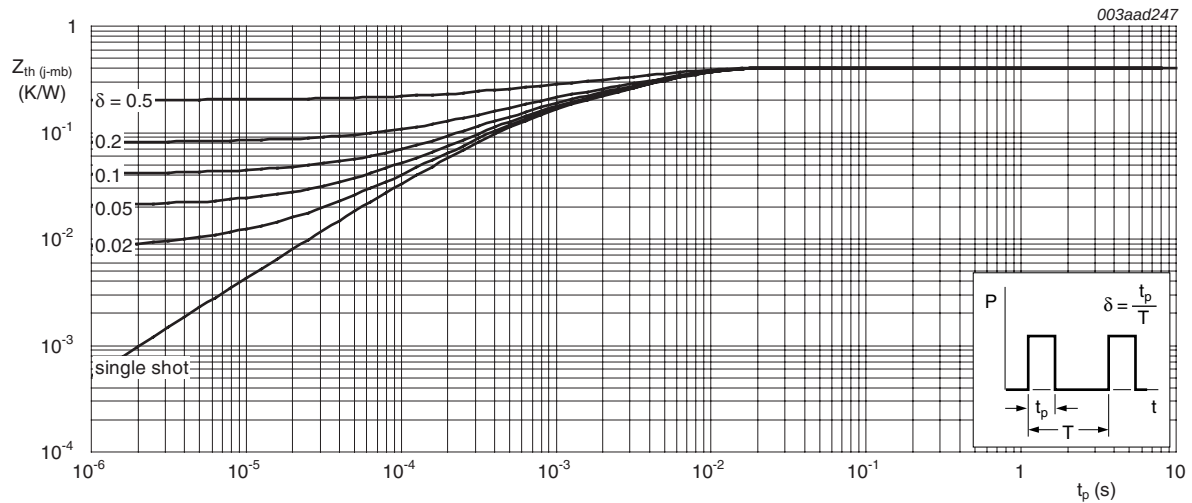


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$; $V_{GS} = 0\ \text{V}$; $T_j = -55\ ^\circ\text{C}$	75	-	-	V
		$I_D = 250\ \mu\text{A}$; $V_{GS} = 0\ \text{V}$; $T_j = 25\ ^\circ\text{C}$	80	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\ \text{mA}$; $V_{DS} = V_{GS}$; $T_j = 175\ ^\circ\text{C}$; see Figure 10 and 11	1	-	-	V
		$I_D = 1\ \text{mA}$; $V_{DS} = V_{GS}$; $T_j = -55\ ^\circ\text{C}$; see Figure 10 and 11	-	-	4.6	V
		$I_D = 1\ \text{mA}$; $V_{DS} = V_{GS}$; $T_j = 25\ ^\circ\text{C}$; see Figure 10 and 11	2	3	4	V
I_{DSS}	drain leakage current	$V_{DS} = 80\ \text{V}$; $V_{GS} = 0\ \text{V}$; $T_j = 25\ ^\circ\text{C}$	-	-	3	μA
		$V_{DS} = 80\ \text{V}$; $V_{GS} = 0\ \text{V}$; $T_j = 125\ ^\circ\text{C}$	-	-	80	μA
I_{GSS}	gate leakage current	$V_{GS} = -20\ \text{V}$; $V_{DS} = 0\ \text{V}$; $T_j = 25\ ^\circ\text{C}$	-	-	100	nA
		$V_{GS} = 20\ \text{V}$; $V_{DS} = 0\ \text{V}$; $T_j = 25\ ^\circ\text{C}$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\ \text{V}$; $I_D = 25\ \text{A}$; $T_j = 150\ ^\circ\text{C}$; see Figure 12	-	-	12.4	mΩ
		$V_{GS} = 10\ \text{V}$; $I_D = 25\ \text{A}$; $T_j = 25\ ^\circ\text{C}$; see Figure 13	[2] -	5.9	6.9	mΩ
R_G	internal gate resistance (AC)	$f = 1\ \text{MHz}$	-	0.75	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 0\ \text{A}$; $V_{DS} = 0\ \text{V}$; $V_{GS} = 10\ \text{V}$	-	61	-	nC
		$I_D = 25\ \text{A}$; $V_{DS} = 40\ \text{V}$; $V_{GS} = 10\ \text{V}$; see Figure 14 and 15	-	71	-	nC
Q_{GS}	gate-source charge		-	19	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	13.2	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	5.8	-	nC
Q_{GD}	gate-drain charge		-	16	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25\ \text{A}$; $V_{DS} = 40\ \text{V}$; see Figure 15	-	4.3	-	V
C_{iss}	input capacitance	$V_{DS} = 12\ \text{V}$; $V_{GS} = 0\ \text{V}$; $f = 1\ \text{MHz}$; $T_j = 25\ ^\circ\text{C}$; see Figure 16	-	4502	-	pF
C_{oss}	output capacitance		-	412	-	pF
C_{rss}	reverse transfer capacitance		-	221	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 12\ \text{V}$; $R_L = 0.5\ \Omega$; $V_{GS} = 10\ \text{V}$; $R_{G(ext)} = 4.7\ \Omega$	-	26	-	ns
t_r	rise time		-	24	-	ns
$t_{d(off)}$	turn-off delay time		-	57	-	ns
t_f	fall time		-	22	-	ns

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25\text{ A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ °C}$; see Figure 17	-	0.78	1.2	V
t_{rr}	reverse recovery time	$I_S = 50\text{ A}$; $di_S/dt = 100\text{ A/}\mu\text{s}$; $V_{GS} = 0\text{ V}$;	-	48	-	ns
Q_r	recovered charge	$V_{DS} = 40\text{ V}$	-	82	-	nC

[1] Tested to JEDEC standards where applicable.

[2] Measured 3 mm from package.

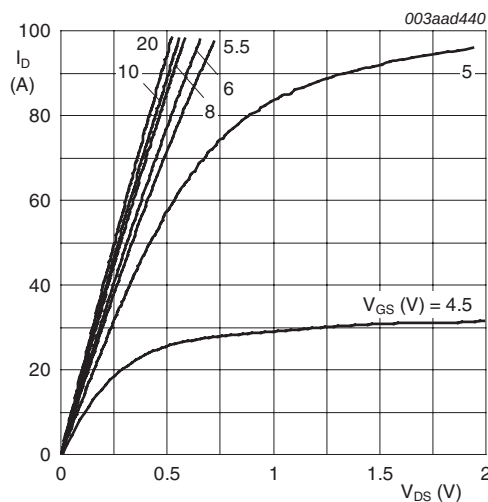
 $T_j = 25\text{ °C}; t_p = 300\text{ }\mu\text{s}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

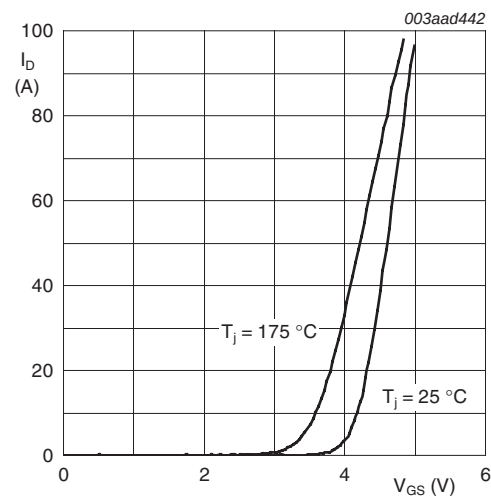
 $V_{DS} = 15\text{ V}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

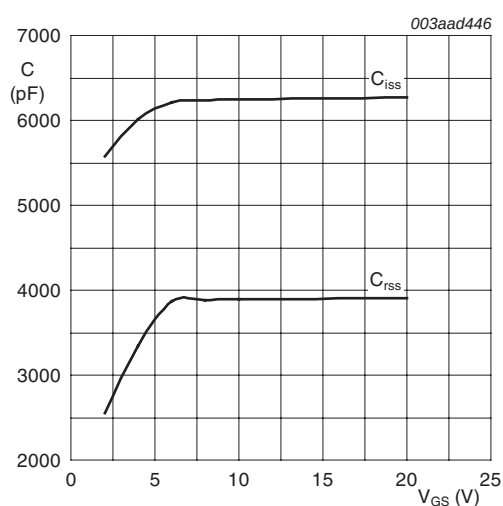
 $V_{DS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

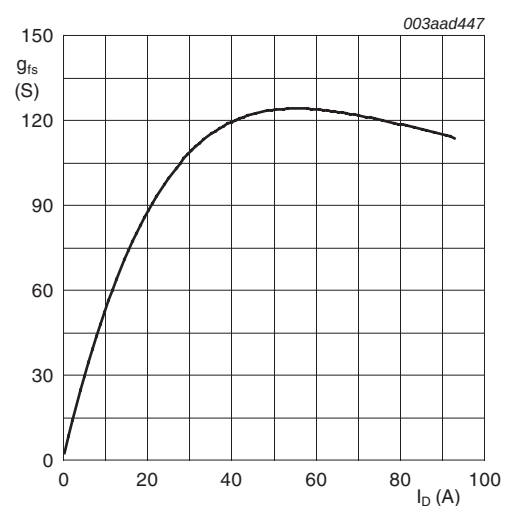
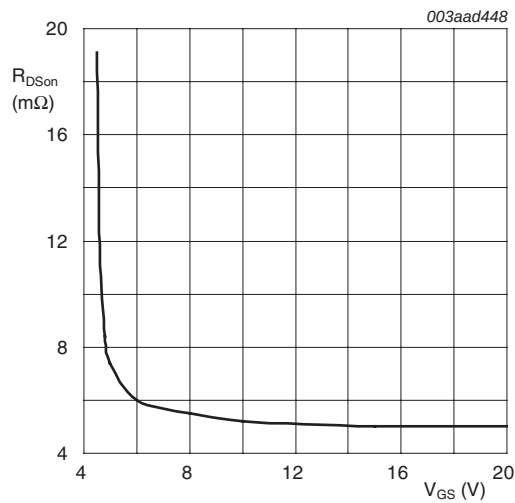
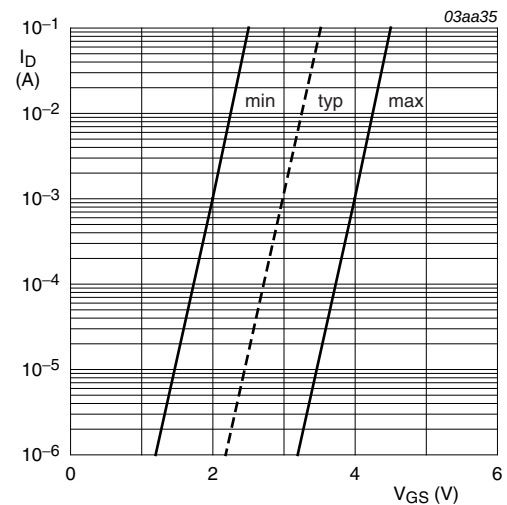
 $T_j = 25\text{ °C}; V_{DS} = 15\text{ V}$

Fig 8. Forward transconductance as a function of drain current; typical values



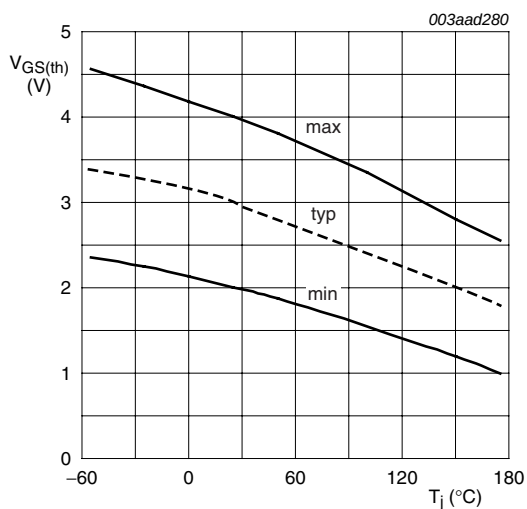
$$T_j = 25^\circ\text{C}; I_D = 25\text{A}$$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



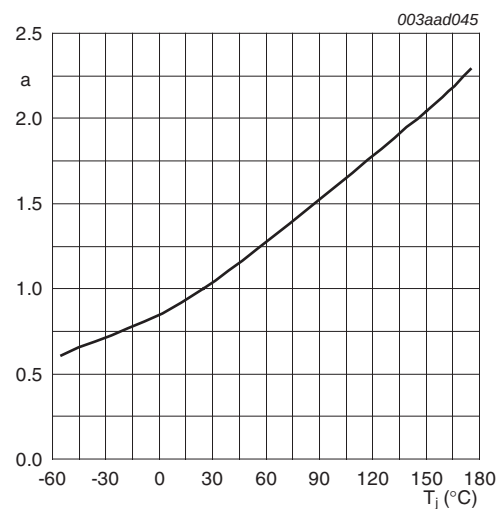
$$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



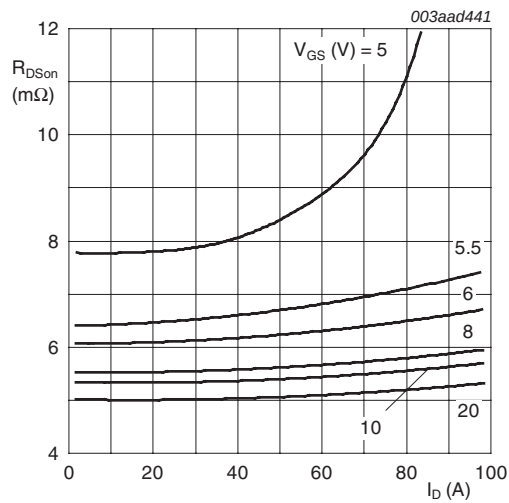
$$I_D = 1\text{ mA}; V_{DS} = V_{GS}$$

Fig 11. Gate-source threshold voltage as a function of junction temperature



$$a = \frac{R_{DS(on)}}{R_{DS(on)(25^\circ\text{C})}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



$$T_j = 25^\circ\text{C}; t_p = 300\mu\text{s}$$

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

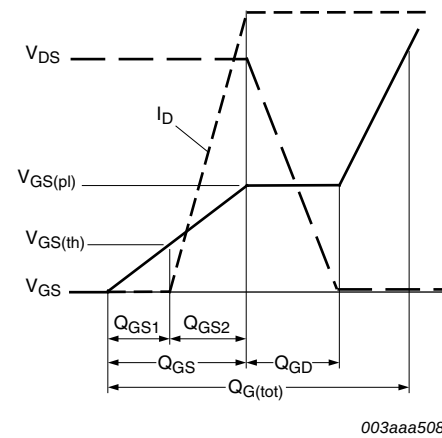
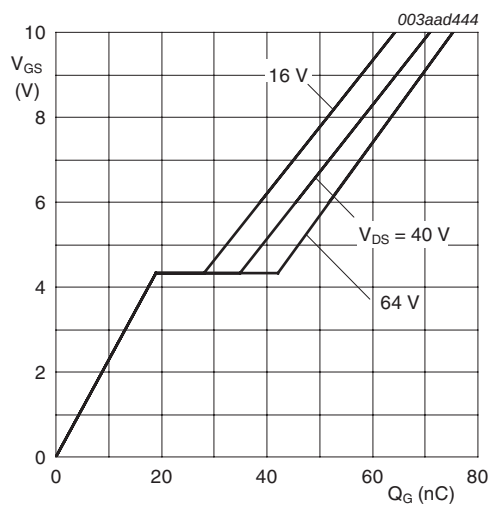
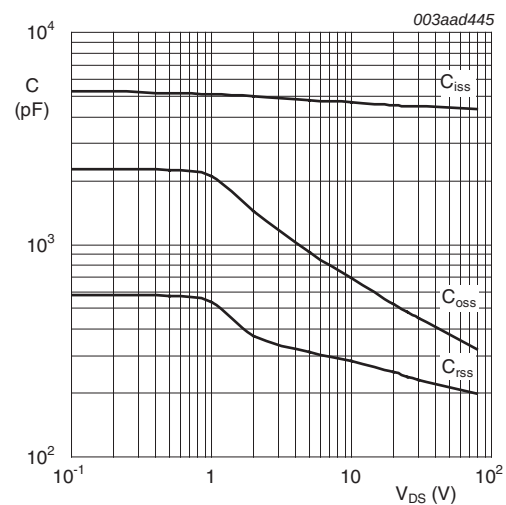


Fig 14. Gate charge waveform definitions



$$T_j = 25^\circ\text{C}; I_D = 25\text{A}$$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$$V_{GS} = 0\text{V}; f = 1\text{MHz}$$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

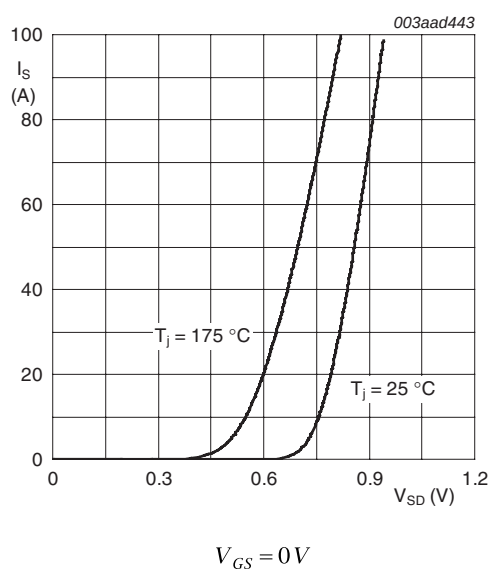
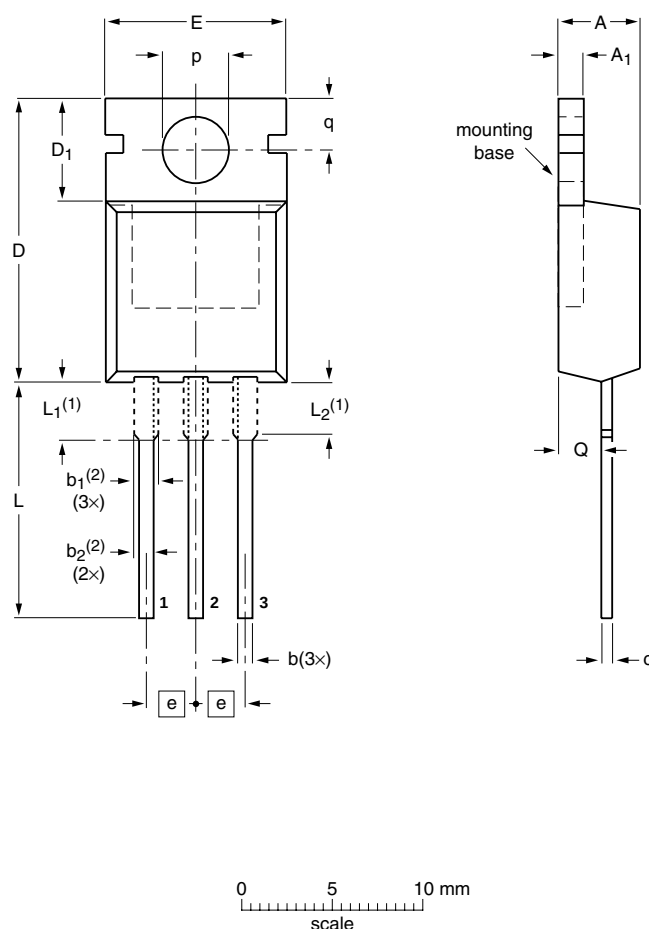


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ (2)	b ₂ (2)	c	D	D ₁	E	e	L	L ₁ (1)	L ₂ (1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- Lead shoulder designs may vary.
- Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

Fig 18. Package outline SOT78 (TO-220AB)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN6R5-80PS_1	20100309	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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For sales office addresses, please send an email to: salesaddresses@nxp.com

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